T816 2800-54-65

Key Parameters

V_{DSM}	5400~6500	V
$I_{T(AV)}$	2800	A
I_{TSM}	45	kA
V_{TO}	1.18	V
r_T	0.274	mΩ

Applications

- SVC
- Motor drive
- Industry converter

Features

- Double-side cooling
- High power capability
- Low loss

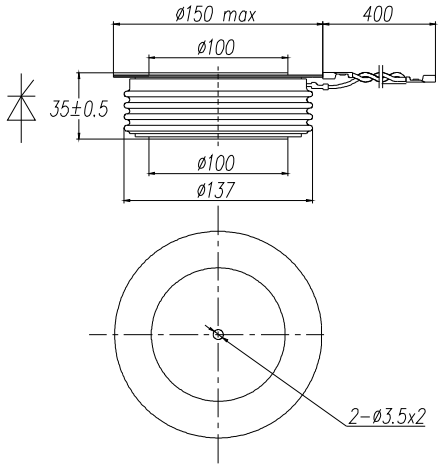
Thermal & Mechanical Data

Symb.	Parameter	Min	Type	Max	Unit
R_{thjc}	Thermal Resistance Junction to Case	-	-	0.0057	K / W
R_{thcs}	Thermal Resistance Case ro Heatsink	-	-	0.0015	K / W
T_{vj}	Junction Temperature	-40	-	125	°C
T_{stg}	Storage Temperature	-40	-	140	°C
F	Mounting Force	-	90	-	kN
m	Weight	-	2.8	-	kg

Voltage Ratings

Device Type	V_{DSM}/V_{RSM}(V)	Test Conditions
T816 2800-54	5400	T_{vj} = 125 °C
T816 2800-58	5800	I_{DRM} = 600 mA
T816 2800-62	6200	I_{RRM} = 600 mA
T816 2800-65	6500	
		$V_{DM}=V_{DRM}$, $V_{RM}=V_{RRM}$
		t_p = 10 ms
		$V_{DRM}=V_{DSM}-900$
		$V_{RRM}=V_{RSM}-900$

Outline



Current Ratings

Symb.	Parameter	Test Conditions	Min	Type	Max	Unit
$I_{T(AV)}$	Mean On-State Current	Half Sine Wave, T_C=70 °C	-	-	2800	A
$I_{T(RMS)}$	RMS On-State Current	T_C =70 °C	-	-	4396	A
I_{TSM}	Surge (non-repetitive) On-State Current	10ms, Half Sine Wave, T_C =125 °C, V_R = 0	-	-	45	kA
I^2t	Limiting load integral	Sine Wave, 10ms	-	-	1013	10^4A^2s

1

T816 2800-54-65

Characteristics

Symb.	Parameter	Test Conditions	Min	Type	Max	Unit
V_{TM}	Peak on-state voltage	T_{vj} = 125 °C, I_{TM} = 3000 A	-	-	2.0	V
I_{DRM}	Forward leakage current	T_{vj} = 125 °C, V_{DRM}	-	-	600	mA
I_{RRM}	Reverse leakage current	T_{vj} = 125 °C, V_{RRM}	-	-	600	mA
V_{TO}	Threshold voltage	T_{vj} = 125 °C	-	-	1.18	V
r_T	Slope resistance	T_{vj} = 125 °C	-	-	0.274	mΩ
I_H	Holding current	T_{vj} = 25 °C	-	-	200	mA
I_L	Latching current	T_{vj} = 25 °C	-	-	1000	mA

Dynamic Parameters

Symb.	Parameter	Test Conditions		Min	Type	Max	Unit
dv/dt	Critical rate of rise of off-state voltage	T_{vj} = 125 °C, 0.67V_{DRM}		2000	-	-	V/μs
di/dt	Critical rate of rise of on-state current	T_{vj} =125°C, V_{DM} =0.67V_{DRM}, I_{TM} =3000A I_{FG} = 2 A, tr = 0.5 μs	f = 1 Hz	-	-	1000	A/μs
			f = 50 Hz	-	-	200	
t_d	Delay time	T_{vj} = 25 °C, V_{DM} = 0.5V_{DRM}, I_{TM} = 3000 A I_{FG} = 2 A, tr = 0.5 μs		-	-	3.0	μs
t_q	Turn-off time	T_{vj}=125°C, V_{DM}=0.67V_{DRM}, dv/dt=20V/μs, V_R=200V di_T/dt = -1.5 A/μs, I_T = 2000 A		-	800	-	μs
Q_{rr}	Recovery Charge	T_{vj} = 125°C, di_T/dt = -1.5A/μs, V_R = 200V, I_T = 2000A		4000	-	5000	μC
I_{rr}	Reverse recovery current			70	-	85	A

Gate Parameters

Symb.	Parameter	Test Conditions	Min	Type	Max	Unit
I_{GT}	Gate trigger current	T_{vj} = 25 °C	-	-	300	mA
V_{GT}	Gate trigger voltage	T_{vj} = 25 °C	-	-	3	V
V_{GD}	Gate non-trigger voltage	T_{vj} = 125 °C, V_D = 0.4V_{DRM}	0.3	-	-	V
V_{FGM}	Peak forward gate voltage		-	-	12	V
V_{RGM}	Peak reverse gate voltage		-	-	5	V
I_{FGM}	Peak forward gate current		-	-	4	A
P_{GM}	Gate power losses		-	-	20	W
$P_{G(AV)}$	Gate power losses (mean)		-	-	4	W

T816 2800-54-65

Max. on-state characteristic model

$$V_T = A + B \cdot \ln(I_T) + C \cdot I_T + D \cdot \sqrt{I_T}$$

	25 °C	125 °C
A	2.713560	-0.359810
B	-0.356158	0.2491390
C	-0.0000275	0.0002321
D	0.0400014	-0.0059296

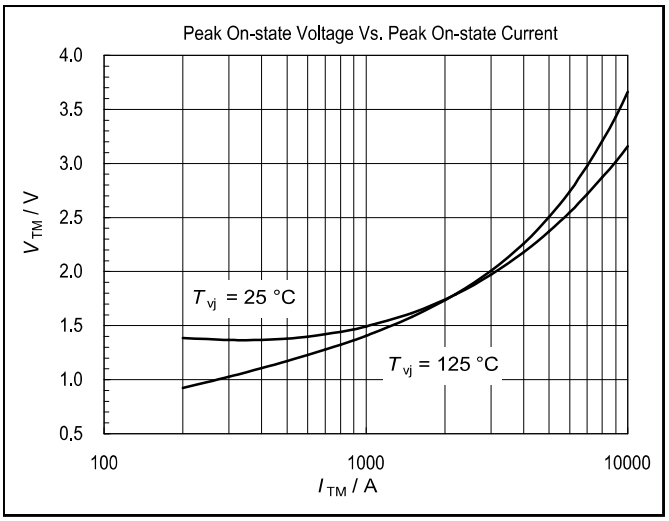


Fig1. Peak On-state Voltage Vs. Peak On-state Current

Transient thermal impedance function (double side cooled)

$$R_{thjc}(t) = \sum_{i=1}^{n} R_{thi} \cdot \left(1 - e^{-\frac{t}{\tau_i}}\right)$$

i	1	2	3	4
R_{thi} (K/kW)	3.709	1.262	0.475	0.251
τ_i (s)	0.8296	0.1107	0.0114	0.0024

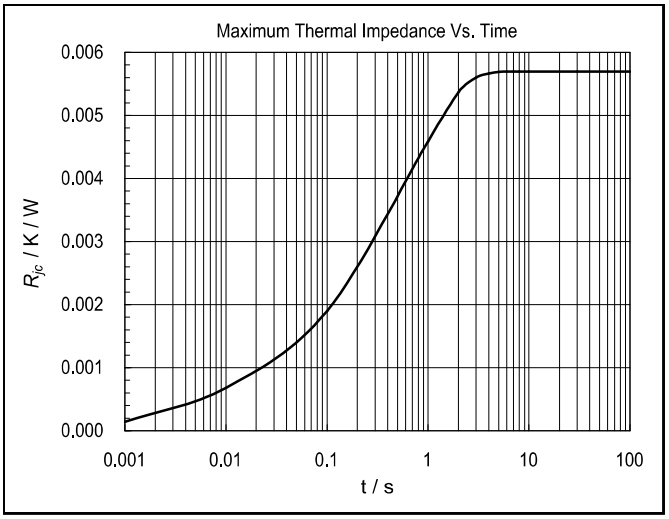


Fig2. Maximum Thermal Impedance Vs. Time

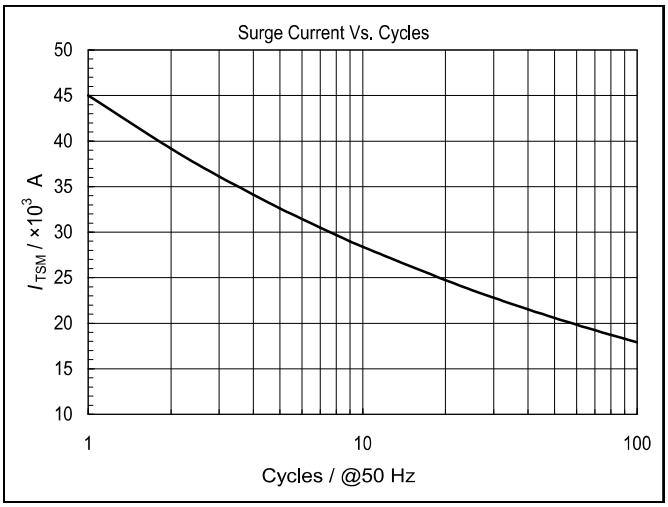


Fig3. Surge Current Vs. Cycles

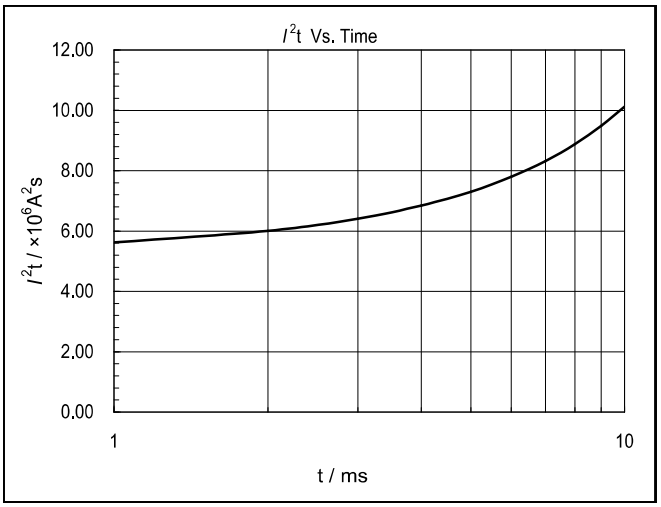


Fig4. I^2t Vs. Time

T816 2800-54-65

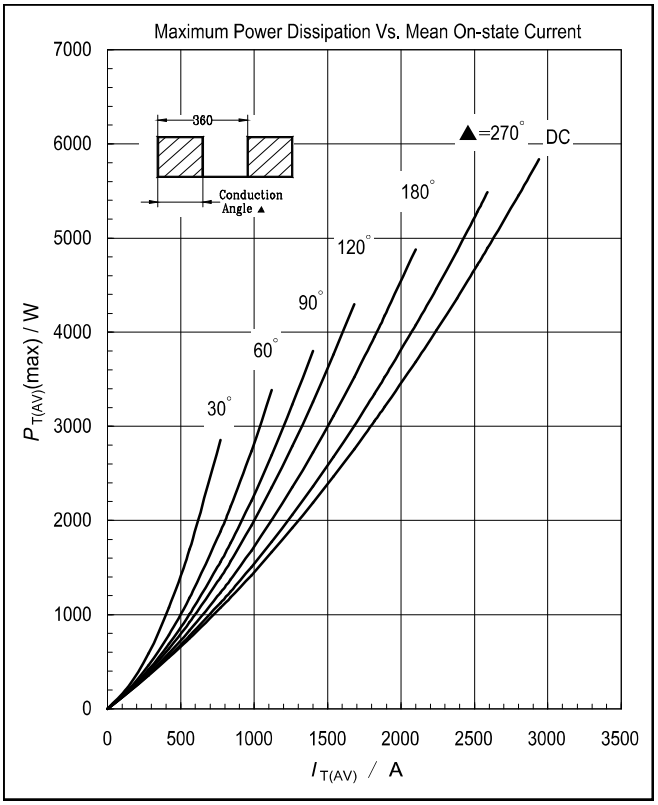


Fig5. Maximum Power Dissipation Vs. Mean On-state Current

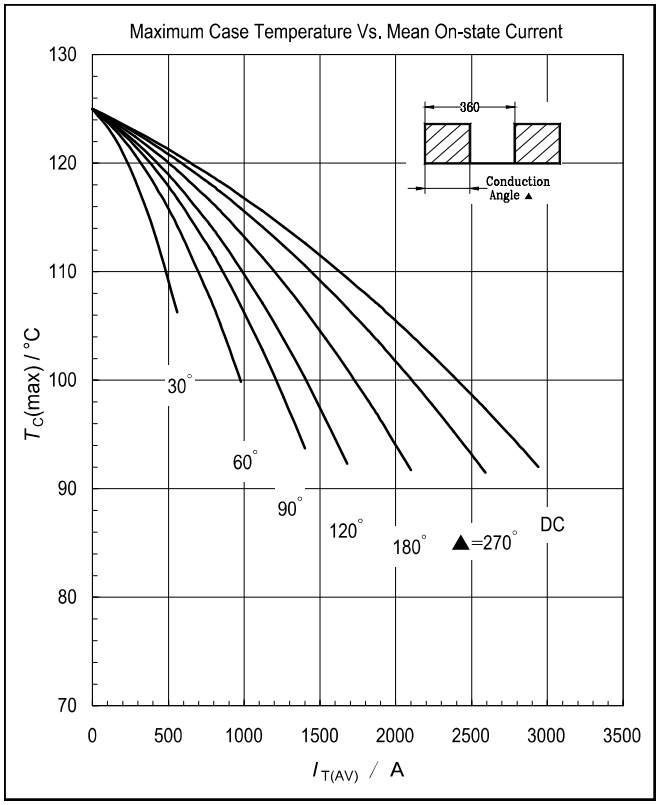


Fig6. Maximum Case Temperature Vs. Mean On-state Current

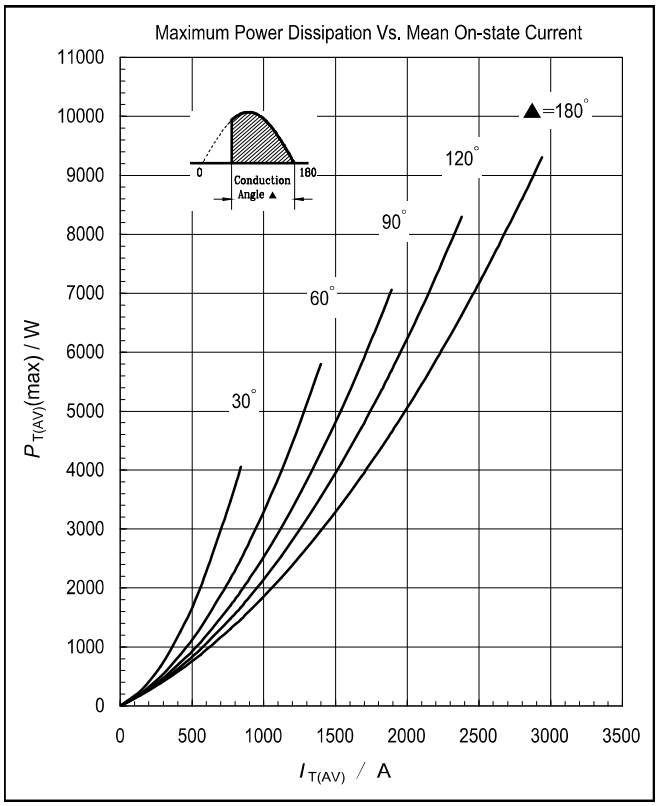


Fig7. Maximum Power Dissipation Vs. Mean On-state Current

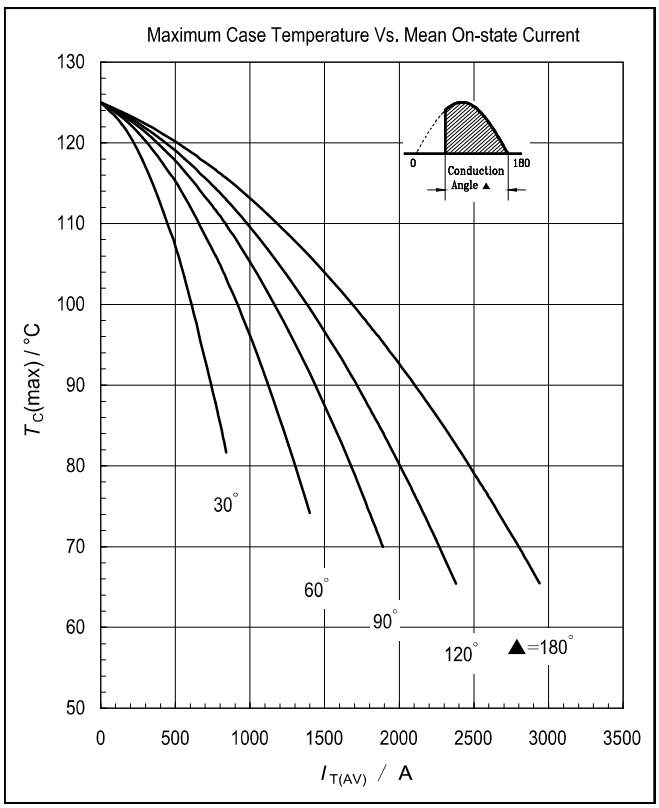


Fig8. Maximum Case Temperature Vs. Mean On-state Current

T816 2800-54-65

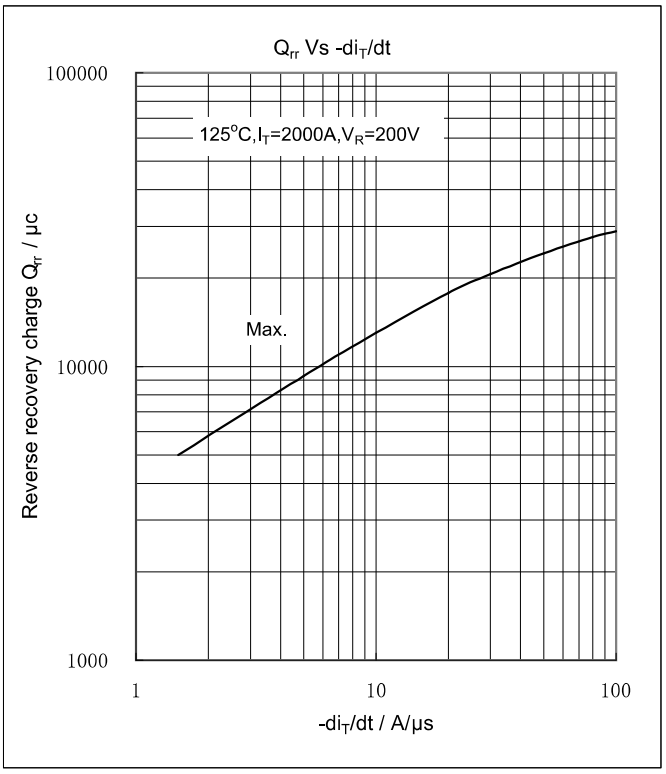


Fig9. Reverse recovery charge Vs. $-di_T/dt$

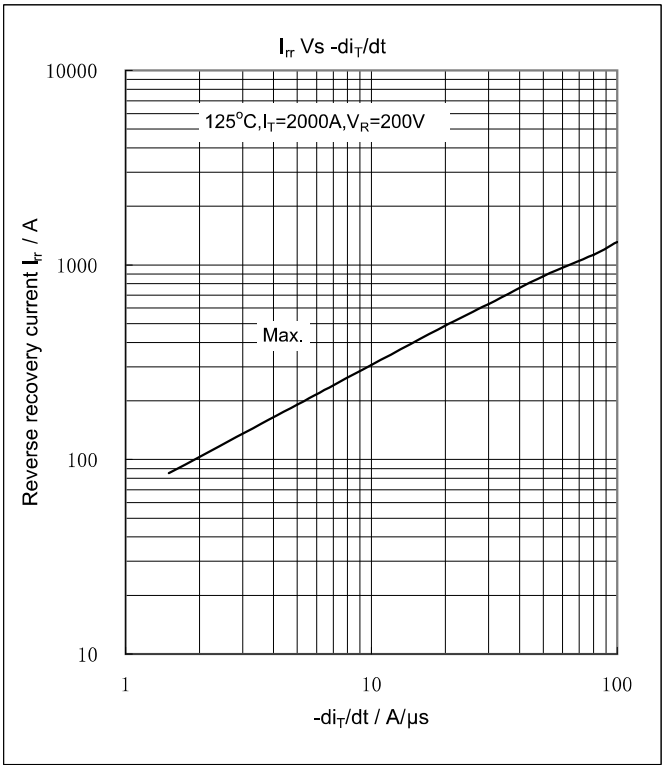


Fig10. Reverse recovery current Vs. $-di_T/dt$

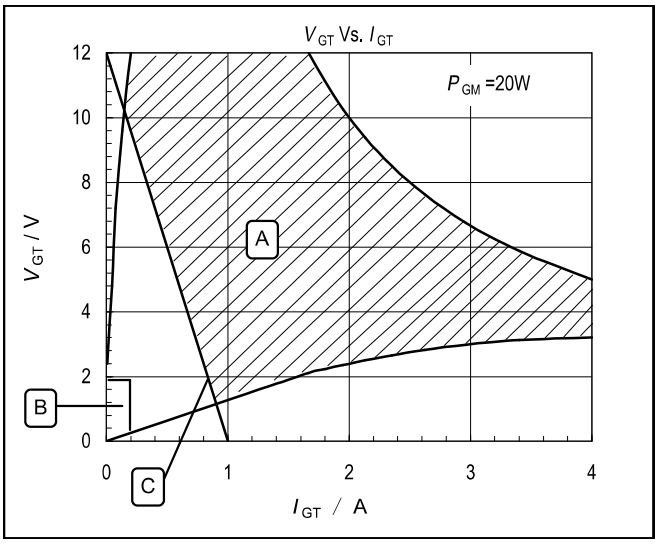


Fig11. V_{GT} Vs. I_{GT}

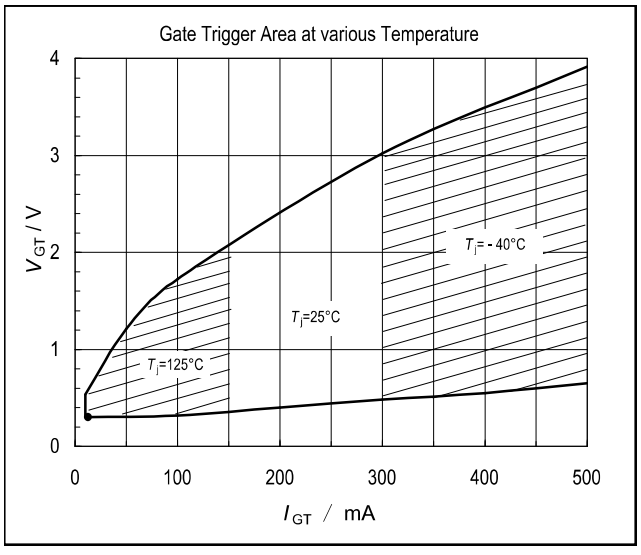


Fig12. Gate Trigger Area at various Temperature

A is Recommended Triggering Area.

B is Unreliable Triggering Area.

C is Recommended Gate Load Line.